# **Amplifier Transistors**

# **NPN Silicon**

#### **Features**

 These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



Rating	Symbol	Value	Unit
Collector - Emitter Voltage	$V_{CEO}$	45	Vdc
Collector - Base Voltage	$V_{CBO}$	55	Vdc
Emitter - Base Voltage	$V_{EBO}$	6.0	Vdc
Collector Current - Continuous	Ic	200	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation (Note 1)  T <sub>A</sub> = 25°C	P <sub>D</sub>	150	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	833	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

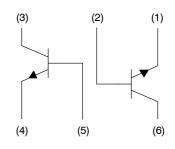
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

 Device mounted on FR4 glass epoxy printed circuit board using the minimum recommended foot print.



## ON Semiconductor®

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SC-88 (SOT-363) CASE 419B

#### **MARKING DIAGRAM**



1T = Specific Device Code

M = Date Code

■ = Pb-Free Package

(Note: Microdot may be in either location)

## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>		
MBT6429DW1T1G	SC-88 (Pb-Free)	3000 / Tape & Reel		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	<u>.</u>			•
Collector – Emitter Breakdown Voltage (I <sub>C</sub> = 1.0 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)</sub> CEO	45	_	Vdc
Collector – Base Breakdown Voltage $(I_C = 0.1 \text{ mAdc}, I_E = 0)$	V <sub>(BR)</sub> CBO	55	-	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 30 Vdc)	I <sub>CES</sub>	-	0.1	μAdc
Collector Cutoff Current (V <sub>CB</sub> = 30 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	-	0.01	μAdc
Emitter Cutoff Current (V <sub>EB</sub> = 5.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	0.01	μAdc
ON CHARACTERISTICS			-	•
DC Current Gain ( $I_C = 0.01 \text{ mAdc}$ , $V_{CE} = 5.0 \text{ Vdc}$ ) ( $I_C = 0.1 \text{ mAdc}$ , $V_{CE} = 5.0 \text{ Vdc}$ ) ( $I_C = 1.0 \text{ mAdc}$ , $V_{CE} = 5.0 \text{ Vdc}$ ) ( $I_C = 10 \text{ mAdc}$ , $V_{CE} = 5.0 \text{ Vdc}$ )	h <sub>FE</sub>	500 500 500 500	_ 1250 _ _	-
Collector – Emitter Saturation Voltage ( $I_C = 10$ mAdc, $I_B = 0.5$ mAdc) ( $I_C = 100$ mAdc, $I_B = 5.0$ mAdc)	V <sub>CE(sat)</sub>	- -	0.2 0.6	Vdc
Base – Emitter On Voltage (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 5.0 Vdc)	V <sub>BE(on)</sub>	0.56	0.66	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current – Gain – Bandwidth Product (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 5.0 Vdc, f = 100 MHz)	f⊤	100	700	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	-	3.0	pF
Input Capacitance (V <sub>EB</sub> = 0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>ibo</sub>	_	8.0	pF

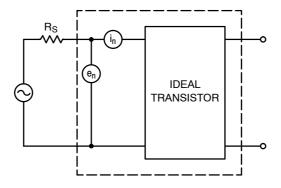
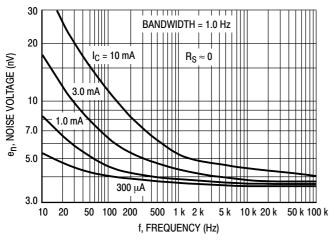


Figure 1. Transistor Noise Model

#### **NOISE CHARACTERISTICS**

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}C)$ 

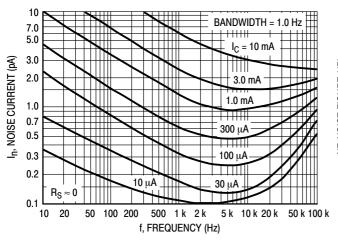
#### **NOISE VOLTAGE**



BANDWIDTH = 1.0 Hz 20 en, NOISE VOLTAGE (nV)  $R_S \approx 0\,$ f = 10 Hz 10 7.0 5.0 3.0 0.01 0.02 0.1 0.2 0.5 1.0 2.0 5.0 0.05 10 IC, COLLECTOR CURRENT (mA)

Figure 2. Effects of Frequency

**Figure 3. Effects of Collector Current** 



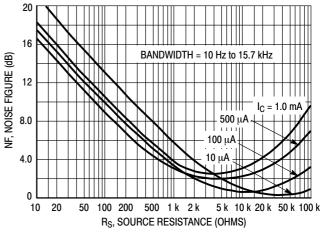
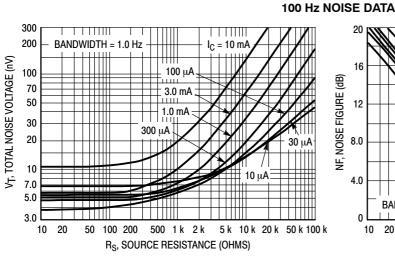


Figure 4. Noise Current

Figure 5. Wideband Noise Figure



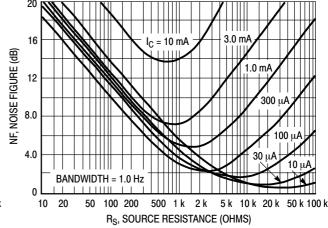


Figure 6. Total Noise Voltage

Figure 7. Noise Figure

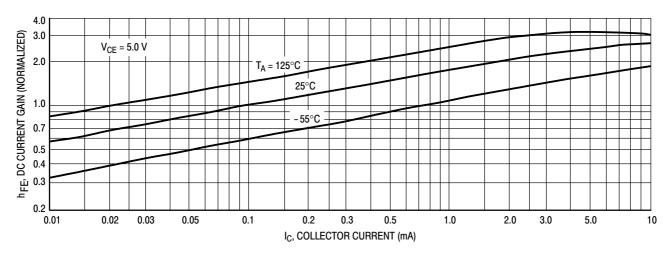


Figure 8. DC Current Gain

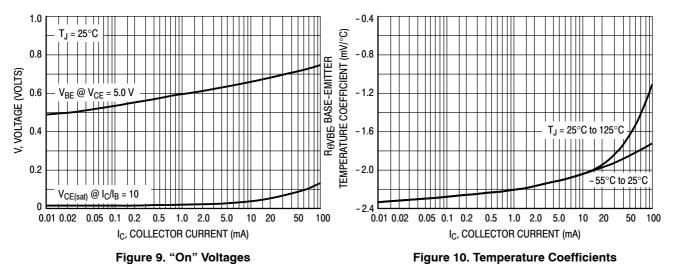


Figure 9. "On" Voltages

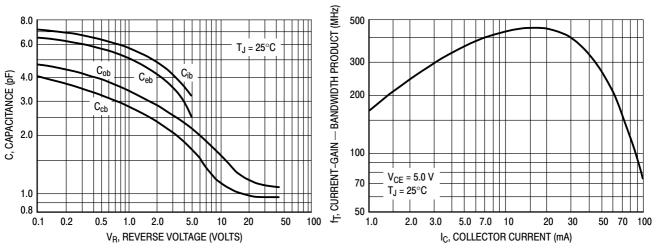


Figure 11. Capacitance

Figure 12. Current-Gain - Bandwidth Product

#### PACKAGE DIMENSIONS

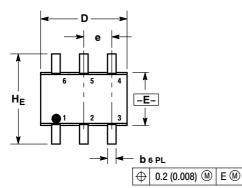
#### SC-88/SC70-6/SOT-363

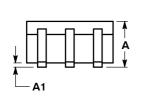
CASE 419B-02 ISSUE W

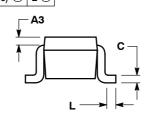
#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
  Y14.5M. 1982.
- 2. CONTROLLING DIMENSION: INCH.
- 3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

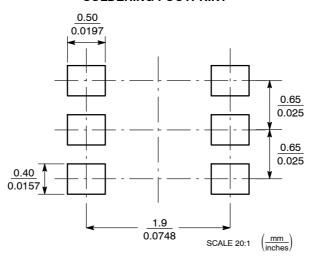
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.80	0.95	1.10	0.031	0.037	0.043
A1	0.00	0.05	0.10	0.000	0.002	0.004
А3		0.20 REF 0.			0.008 REF	
b	0.10	0.21	0.30	0.004	0.008	0.012
С	0.10	0.14	0.25	0.004	0.005	0.010
D	1.80	2.00	2.20	0.070	0.078	0.086
Е	1.15	1.25	1.35	0.045	0.049	0.053
е	0.65 BSC		0.026 BSC		С	
L	0.10	0.20	0.30	0.004	0.008	0.012
ΗF	2.00	2.10	2.20	0.078	0.082	0.086







#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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